

システム設計のための Sパラメタモデリングに関する考察

三堂哲寿
Synopsys Inc.
September 2020



CONFIDENTIAL INFORMATION

The information contained in this presentation is the confidential and proprietary information of Synopsys. You are not permitted to disseminate or use any of the information provided to you in this presentation outside of Synopsys without prior written authorization.

IMPORTANT NOTICE

In the event information in this presentation reflects Synopsys' future plans, such plans are as of the date of this presentation and are subject to change. Synopsys is not obligated to update this presentation or develop the products with the features and functionality discussed in this presentation. Additionally, Synopsys' services and products may only be offered and purchased pursuant to an authorized quote and purchase order or a mutually agreed upon written contract with Synopsys.

Table of Contents

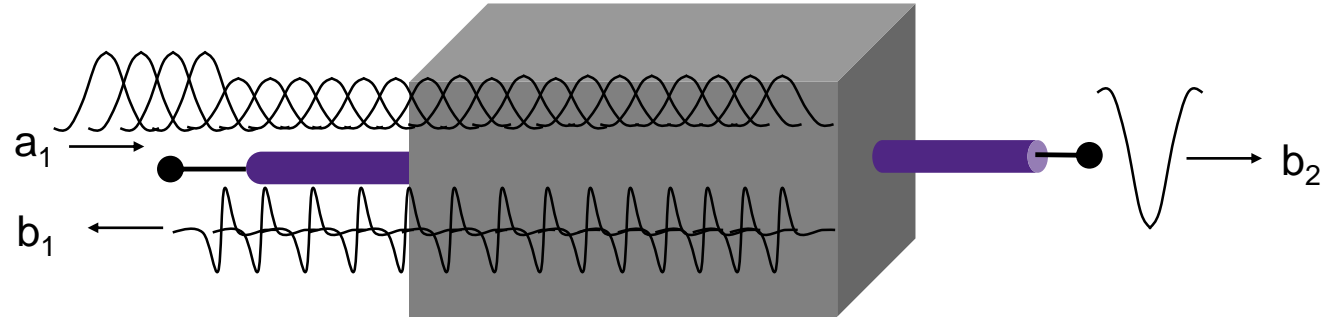
- Introduction
- S-parameter Quality Assessments
 - Checking Causality
- Tips in s-parameter modeling
 - Decoupling Capacitor
 - Multi-segment Transmission Lines
 - Focusing on Partial Network in Large Systems
- Summary

Introductions

S-parameter definitions and insights



Road to the S-parameters

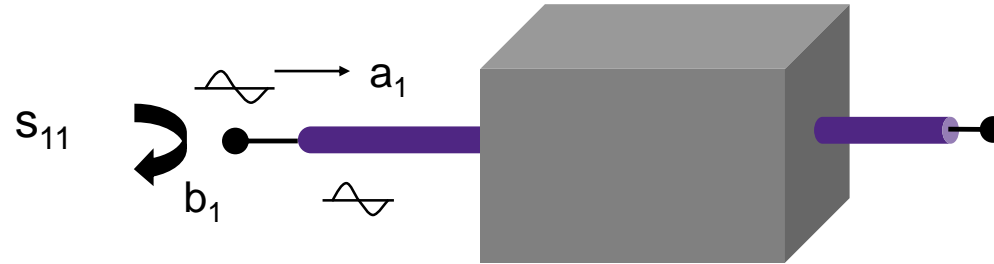


- Simplifying transmission line (EM wave propagation) theory
 - Values for voltage $v(x,t)$ and current $i(x,t)$ along the line can vary dramatically, so they are hard to deal with.
 - A more useful approach is to consider the RF signal as a sum of incident (“ a ”) and reflected (“ b ”) traveling voltage waves.

$$a_1 \sim V_{inc} e^{j(\omega t - \beta x)}$$

$$b_1 \sim V_{ref} e^{j(\omega t + \beta x)}$$

Scattering Parameters



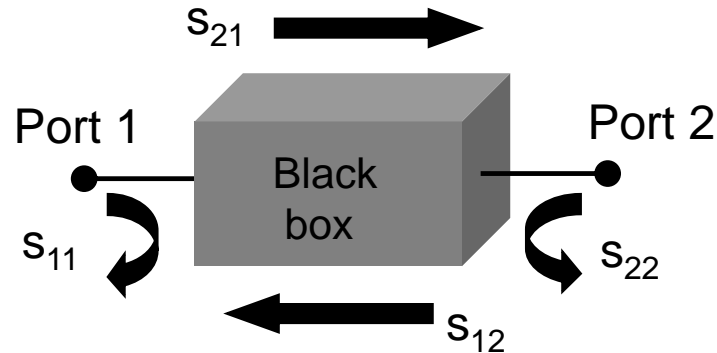
- *S-parameters* represent the complex ratios of these incident and reflected (scattered) voltage waves at a given frequency, e.g.

$$s_{11} = \frac{b_1}{a_1}$$

○○○○ Simpler algebra

- S-parameters are complex numbers: we can make useful calculations using complex arithmetic.
- S-parameters are easily measured by injecting power and measuring reflected & transmitted signals.

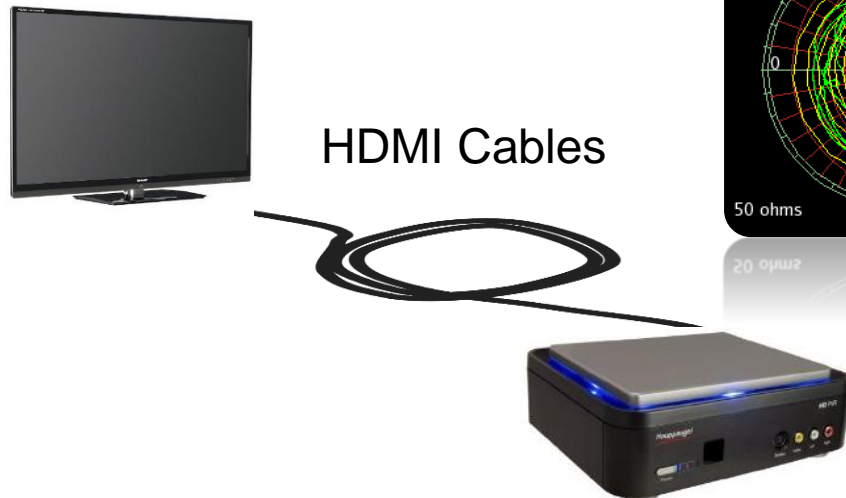
Two-Port Scattering Parameters



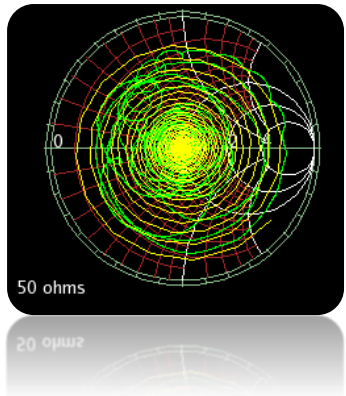
- S_{11} = input reflection coefficient (return loss)
- S_{21} = forward transmission coefficient (gain, Insertion loss)
- S_{12} = reverse transmission coefficient (isolation)
- S_{22} = output reflection coefficient

- S -parameter matrix:
$$\mathbf{S} = \begin{pmatrix} s_{11} & s_{12} \\ s_{21} & s_{22} \end{pmatrix}$$

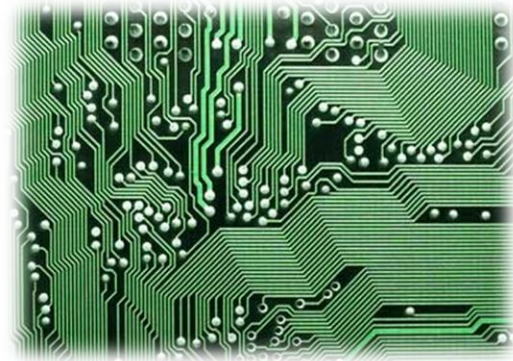
S-Parameter Varieties



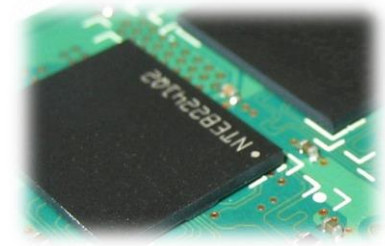
HDMI Cables



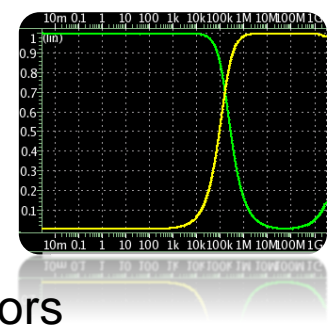
50 ohms

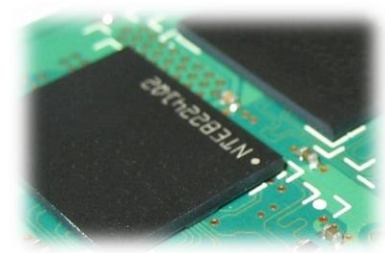


PCB Wires

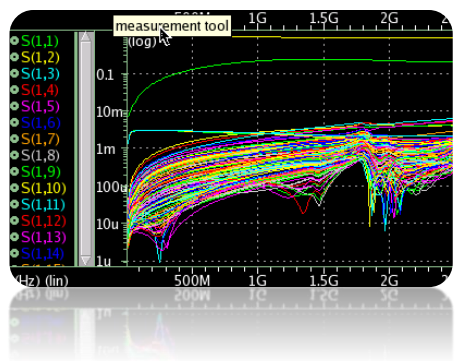


Ceramic Capacitors





IC Packages



S-parameters Advantages & Challenges

Designers

- Useful in system evaluations

- 😊 Measurable
 - Linear(ized) n-port
 - High frequency coverage
- 😊 Smith Chart Display
 - Passive : $|S_{ij}| \leq 1$
 - Impedance matching

Designers

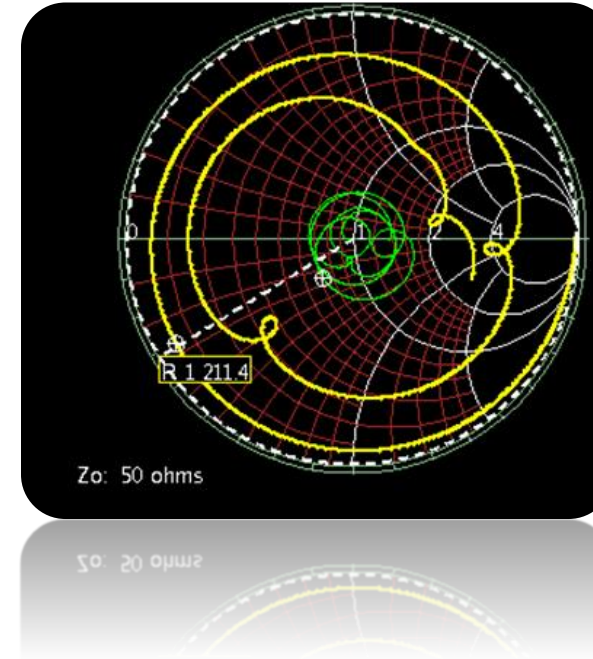
- Useful in IP distribution

- 😊 Black box
- 😊 Distributed network

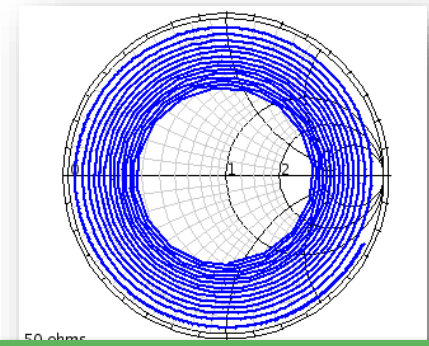
Tools

- Challenges in Simulations

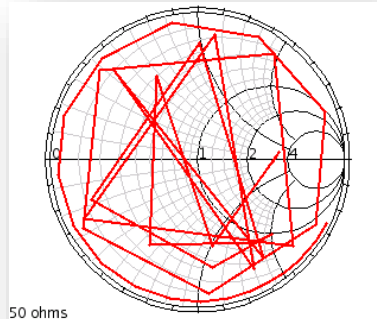
- 😞 Discrete sampling, limited bandwidth
- 😞 Passivity violations, bad terminations
- 😞 $S(f)$ in time domain
- 😞 Black boxed



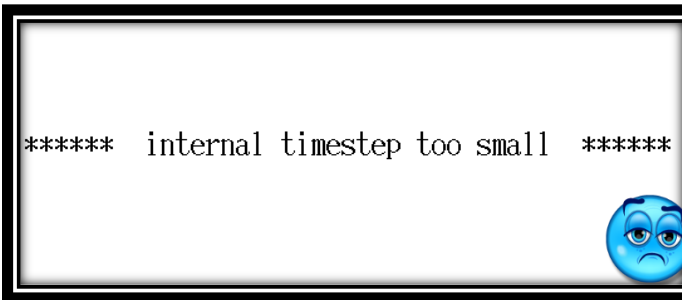
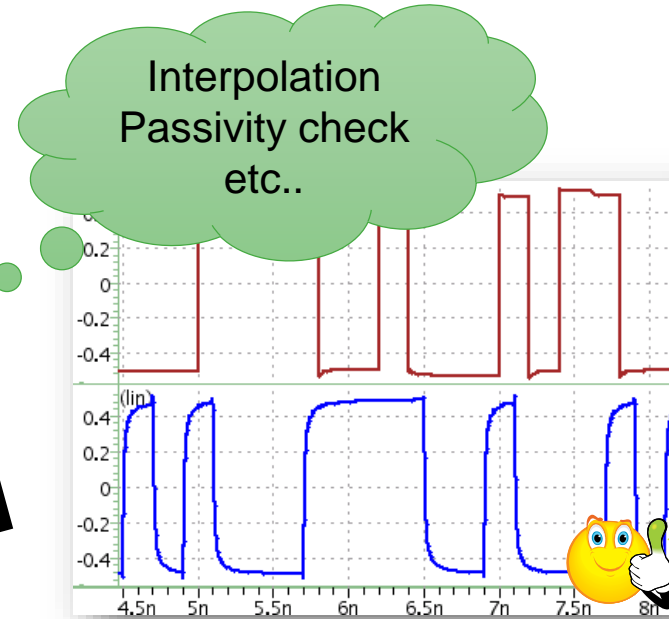
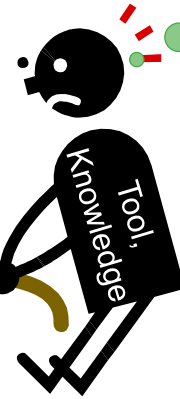
1st Step to Ensure Good Results



good s-parameters

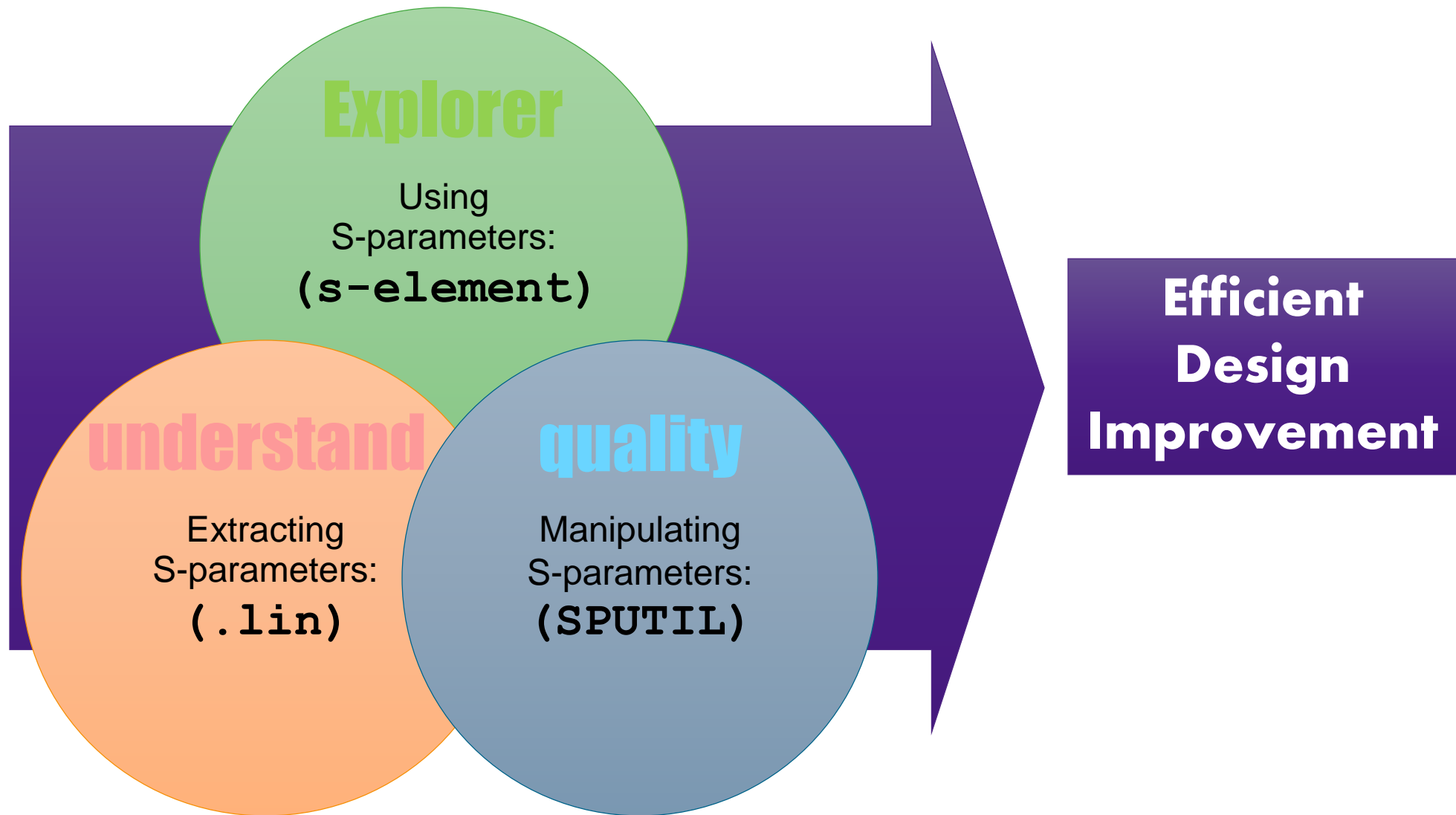


poor s-parameters



Best practice: Please look at your s-parameters before using them

Essentials in Designs with S-parameters



S-parameter Quality Assessments

Passivity, reciprocity, causality and more...



S-parameter Quality Assessment in IEEE P370^[1]

Introduction to the IEEE P370 Standard and its Applications for High Speed Interconnect Characterization

IEEE P370 WorkGroup

DESIGNCON 2020
25th ANNIVERSARY
WHERE THE CHIP MEETS THE BOARD

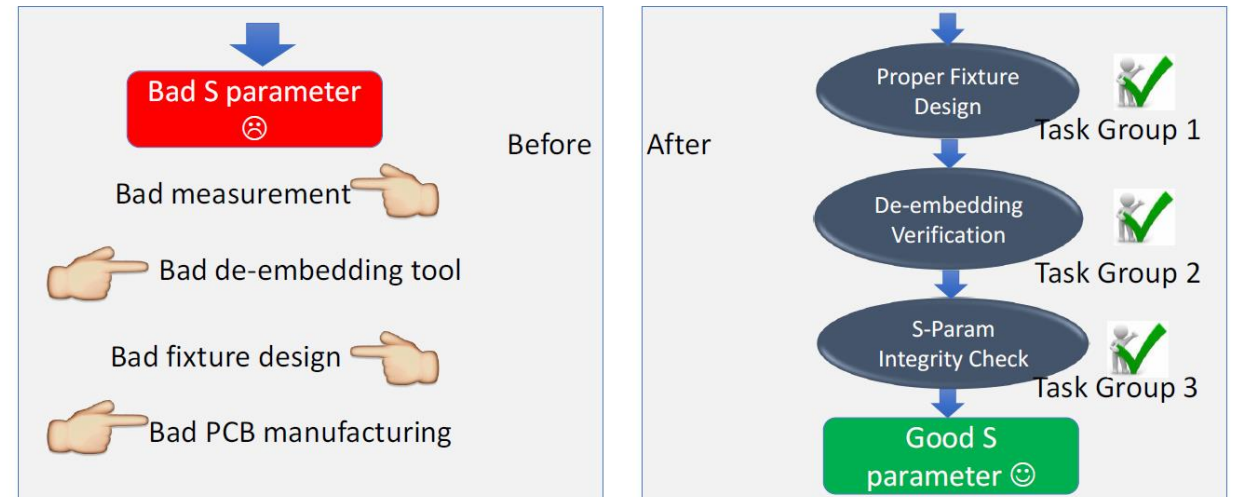


January 28–30, 2020

#DesignCon

informamarkets

P370 Objectives



DESIGNCON 2020
25th ANNIVERSARY
WHERE THE CHIP MEETS THE BOARD



January 28–30, 2020

11 informamarkets

[1] IEEE P370 Work Group,
“Introduction to the IEEE P370 Standard and its Applications for High
Speed Interconnect Characterization,” DesignCon 2020

S-parameter Quality Assessment in IEEE P370^[1]

TG3: S-parameter Integrity and Validation

Problem statement:

- The quality of measured S-parameters of DUT can vary widely. There is no IEEE standard to check and validate the quality of S-parameters before they are distributed for use.

Key P370 contributions:

- A procedure to evaluate the integrity of S-parameters before distribution
- Quantitative criteria on what is the expected impact of imperfection

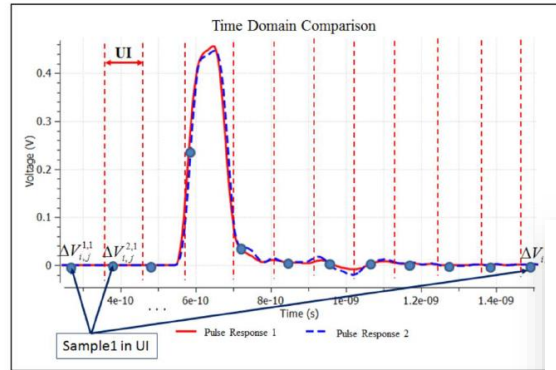
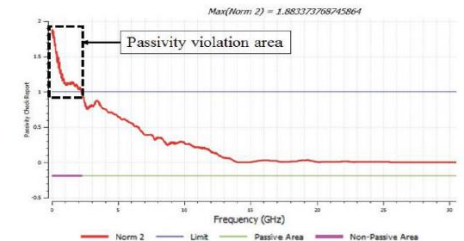
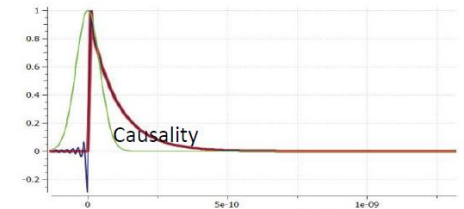


Figure 29 —Time domain estimation in mV unit

S-parameter Quality Estimation

- S-parameters describing a physical system are not perfectly accurate and do not describe it comprehensively;
- It's important to be able to estimate the quality of existing data in order to achieve reliability of the results and conclusions developed based on it
- The goal is to estimate S-parameter quality based on three properties:
 - Passivity
 - Reciprocity
 - Causality



[1] IEEE P370 Work Group,
“Introduction to the IEEE P370 Standard and its Applications for High Speed Interconnect Characterization,” DesignCon 2020

Causality

“consequence should not happen before a cause”



Non-Causality Creates Uncertainty in Transient Sim

- A system is causal if the result (output) comes after the cause (input)
- When system is non-causal, transient (marching in time) analysis cannot identify valid results

$$I_{out}(\omega) = Y(\omega) \cdot V_{in}(\omega)$$

↓

$$out(t) = \int_{-\infty}^{\infty} h(t - \tau) \cdot in(\tau) d\tau$$

Convolution Integral

$out(t)$: output

$in(t)$: input

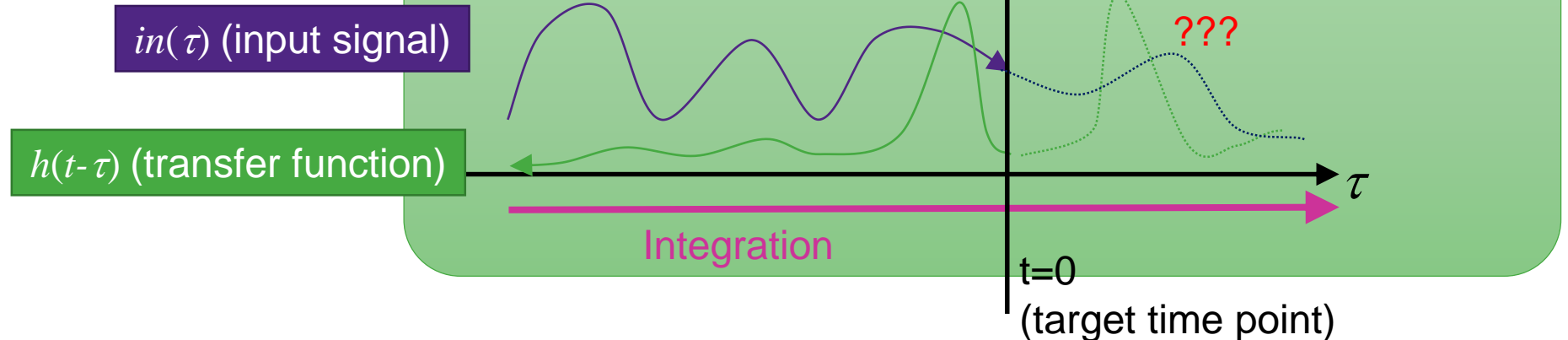
$h(t)$: transfer function

Look at the
output at $t=0$
(for example)

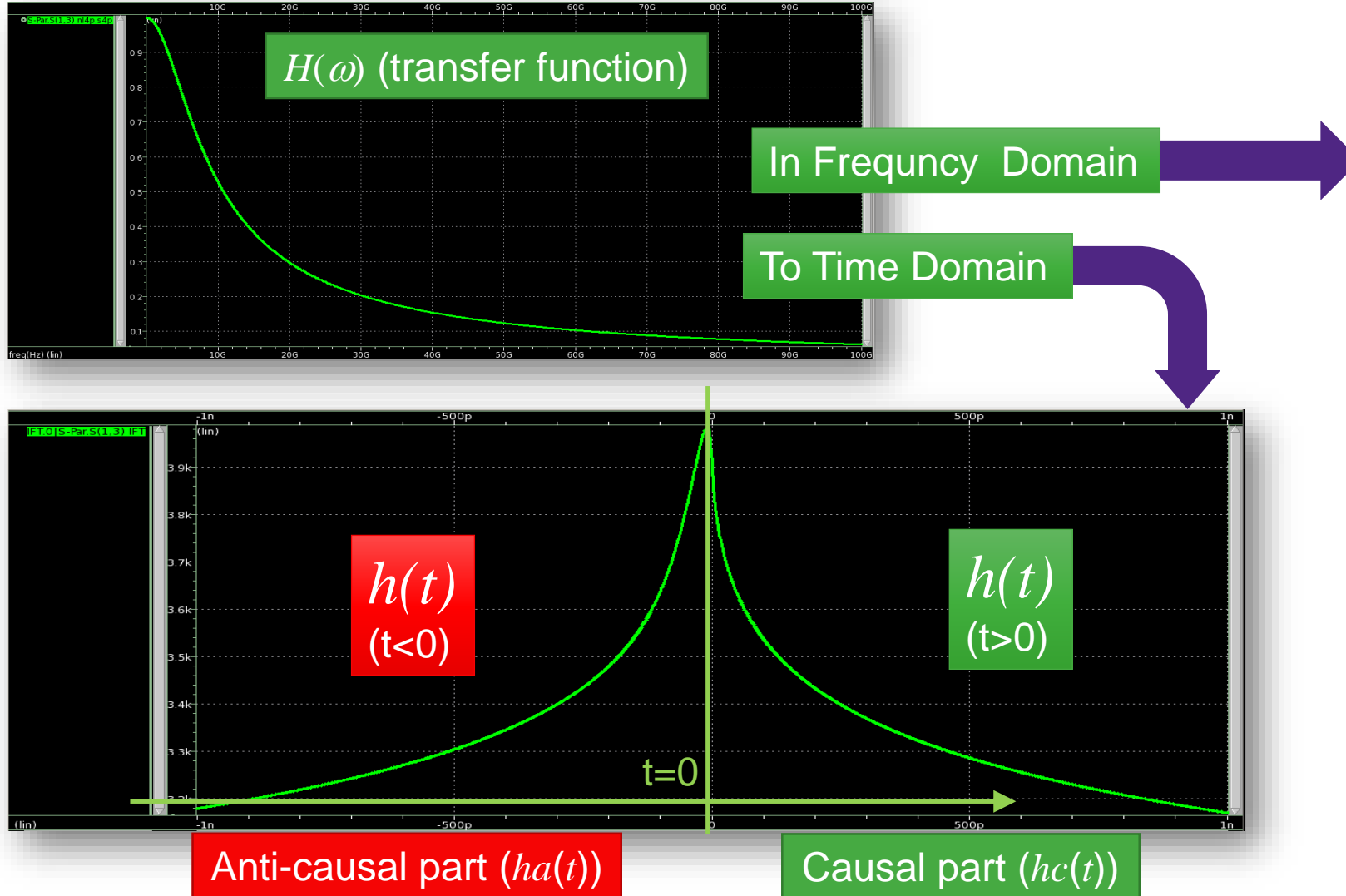
$$out(t=0) = \int_{-\infty}^{\infty} h(-\tau) \cdot in(\tau) d\tau$$
$$= \int_{-\infty}^0 h(-\tau) \cdot in(\tau) d\tau + \int_0^{\infty} h(-\tau) \cdot in(\tau) d\tau$$

Dependency on the past

Dependency on the future!!



Observing Causality Issue



Causal function (R_c : real, I_c : imag) satisfies Kramers-Kronig relations (in Frequency domain)

- $R_c(j\omega) = \frac{1}{\pi} \int_{-\infty}^{\infty} \frac{I_c(j\omega')}{(\omega - \omega')} \cdot d\omega' = H\{I_c(j\omega)\}$
- $I_c(j\omega) = -\frac{1}{\pi} \int_{-\infty}^{\infty} \frac{R_c(j\omega')}{(\omega - \omega')} \cdot d\omega' = -H\{R_c(j\omega)\}$
- Where $H\{\cdot\}$ is the Hilbert Transform.

Typical Causes of non-causal S-Parameters

- Incorrect calibration in measurement
 - E.g. over de-embedding fixture (propagation delay)
- Incorrect physical constant in EM extraction
 - E.g. real-only frequency dependent parameters (skin effect, dielectric loss)
- Insufficient frequency sampling



Tools to Ensure S-parameter Quality (e.g. SPUTIL)

- Format conversion (S/Y/Z Touchstone-v1,v2,CITIfile)
- Merge multiple data files
- Change reference impedance
- Arbitrary re-sampling (w/ inter-/extrapolation, windowing)
- Passivity checker/enforcement
- Causality checker
- Partial view, zero padding (e.g. $S_{dd} \leftrightarrow S_{mixed}$)
- Port swap/reorder/pick
- more...

Causality Checker in SPUTIL

```
TSTONEFILE my_sparam.s2p  
CAUSAL check
```

SPUTIL

- SPUTIL automatically decomposes given system s-parameters into causal and anti-causal part using discrete Hilbert transform in frequency domain
- Feature Selected Validation (FSV) to judge if given data set is causal enough, resulting in the Global Difference Measure (GDM)
- eGDM is a gaussian mapping of average GDM.

eGDM roughly tells :

$0.20 \geq eGDM : \text{poor.}$

$0.65 \geq eGDM > 0.2 : \text{fair.}$

$1.0 \geq eGDM > 0.65 : \text{good.}$

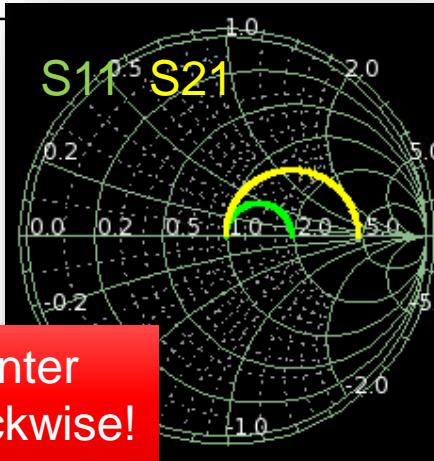
Causality Checker Example

```
P1 1 0 port=1
P2 2 0 port=2
```

```
R1 1 2 50
C1 2 0 -1n
```

DUT

```
.lin format=touchstone
.ac sweepblock=my_swp
.sweepblock my_swp
+ POI 1 0.0
+ DEC 100 1e3 1e9
```



```
S[2,1] avg eGDM is: 1.23e-07
S[1,1] avg eGDM is: 1.23e-07
```

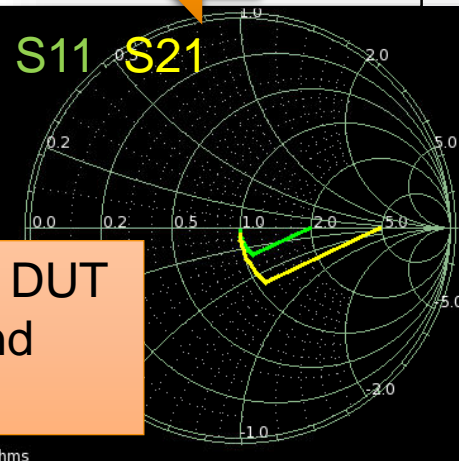
```
P1 1 0 port=1
P2 2 0 port=2
```

```
R1 1 2 50
C1 2 0 1n
```

DUT

corrected

```
.lin format=touchstone
.ac sweepblock=my_swp
.sweepblock my_swp
+ POI 1 0.0
+ DEC 20 1e7 1e8
```



```
S[1,1] avg eGDM is: 0.653
S[2,1] avg eGDM is: 0.653
```

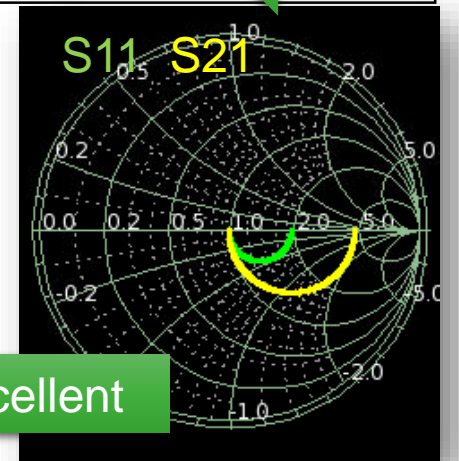
```
P1 1 0 port=1
P2 2 0 port=2
```

```
R1 1 2 50
C1 2 0 1n
```

DUT

widened

```
.lin format=touchstone
.ac sweepblock=my_swp
.sweepblock my_swp
+ POI 1 0.0
+ DEC 200 1e3 20e9
```



```
S[1,1] avg eGDM is: 0.977
S[2,1] avg eGDM is: 0.977
```

Tips in S-parameter Modeling

For High Speed System Designs



[background] Time Domain Analysis with S-parameters



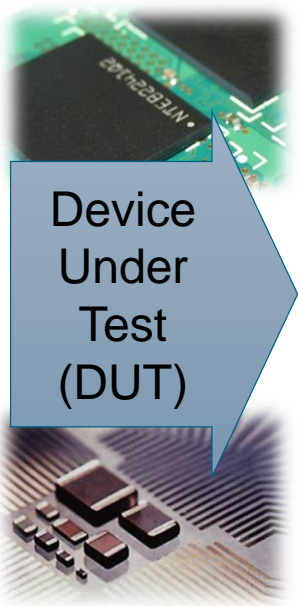
Time-Domain Simulation with Scattering Parameters

$$I_{out}(\omega) = Y(\omega) \cdot V_{in}(\omega) \quad (\text{Eq. 1})$$

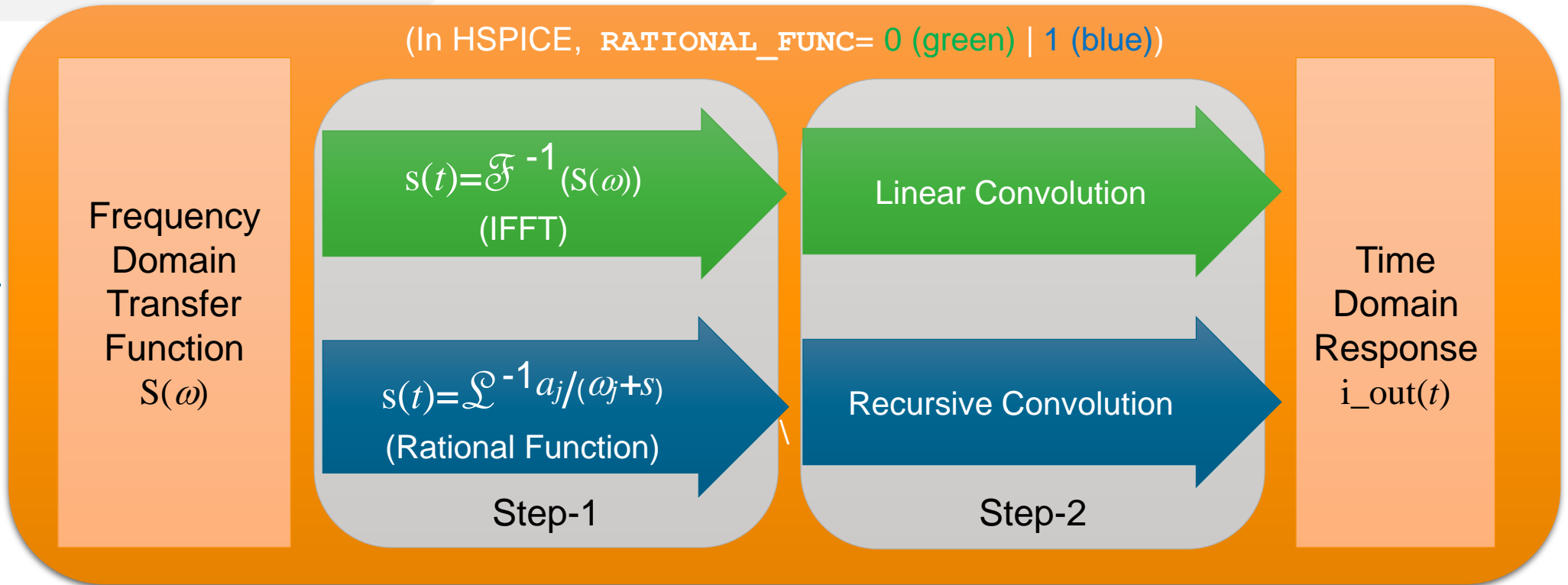
↓ convolution

$$\begin{aligned} i_{out}(t) &= v_{in}(t) * y(t) \\ &= \int_{-\infty}^t y(t-\tau) \cdot v_{in}(\tau) d\tau \quad (\text{Eq. 2}) \end{aligned}$$

- Requires two step analysis
 - Step-1 : prepare transfer function in time domain
 - Step-2 : perform convolution integral to get time domain output



Device Under Test (DUT)



Rational Function Modeling

$$\text{output } y(t_n) = \int_{t_0}^{t_n} h(t_n - \tau) \cdot \text{input } x(\tau) d\tau$$

Linear Convolution (Eq. 2)

$$H(\omega) \cong \frac{1}{\omega_o + s}$$

Rational
Function

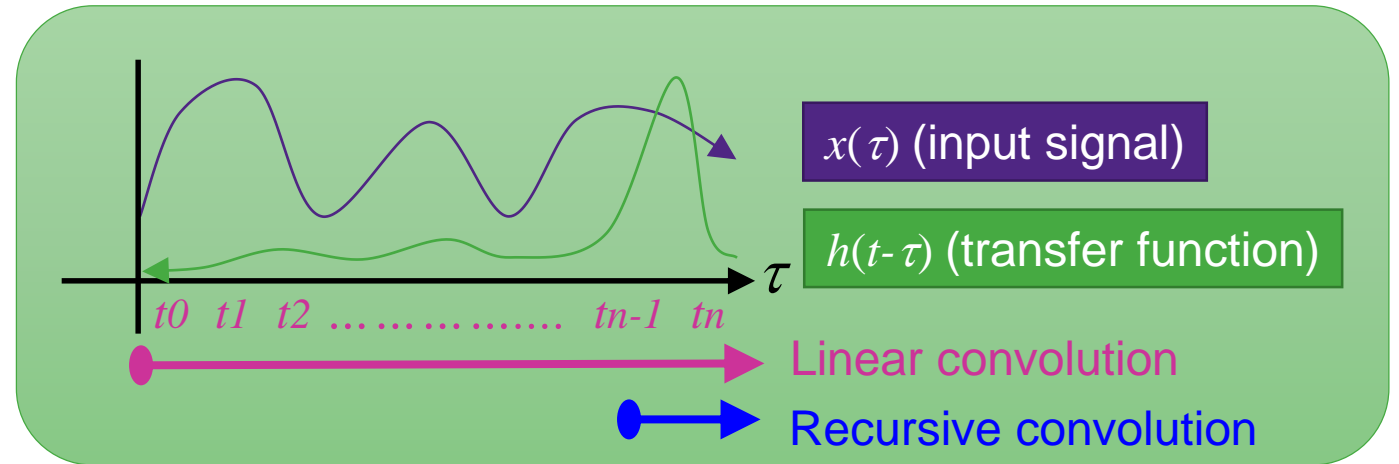
$$h(t) = e^{-\omega_o t}$$

(Eq. 3)

$$y(t_n) = e^{-\omega_o \Delta t} \cdot \text{state variable } y(t_{n-1}) + \int_{t_{n-1}}^{t_n} h(t_n - \tau) \cdot x(\tau) d\tau$$

latest response

Recursive convolution



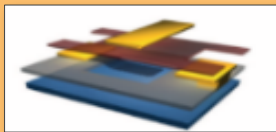
Rational function modeling is ideal for SI/PI simulations

Transient Simulations for SI/PI Analyses

Modeling Challenges

Parasitic Capacitance

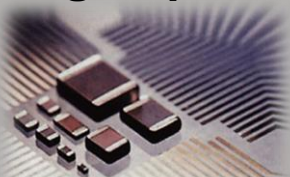
GHz



- Determines [psec] responses

Decoupling Capacitors

kHz

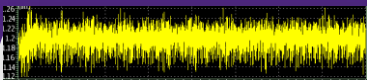


- Determines [msec] stability

High Speed System

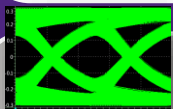


Simulation Challenges



Power Integrity

- SSO analysis to capture both spikes[psec] & drifts[msec] on supply line with deCap



Signal Integrity

- Million bit PRBS analysis to capture extremely low BER

PRBS transient sim runtime

Linear Convolution (*)

Recursive Convolution (*)

500 bits	32 sec	1 sec
5,000 bits	6.4 min	22 sec
50,000 bits	3.5 hr	195 sec

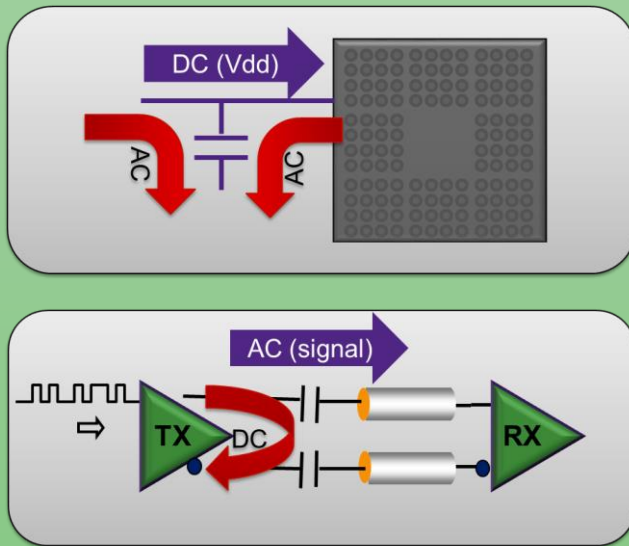
60x

Tip 1 : Decoupling Capacitor

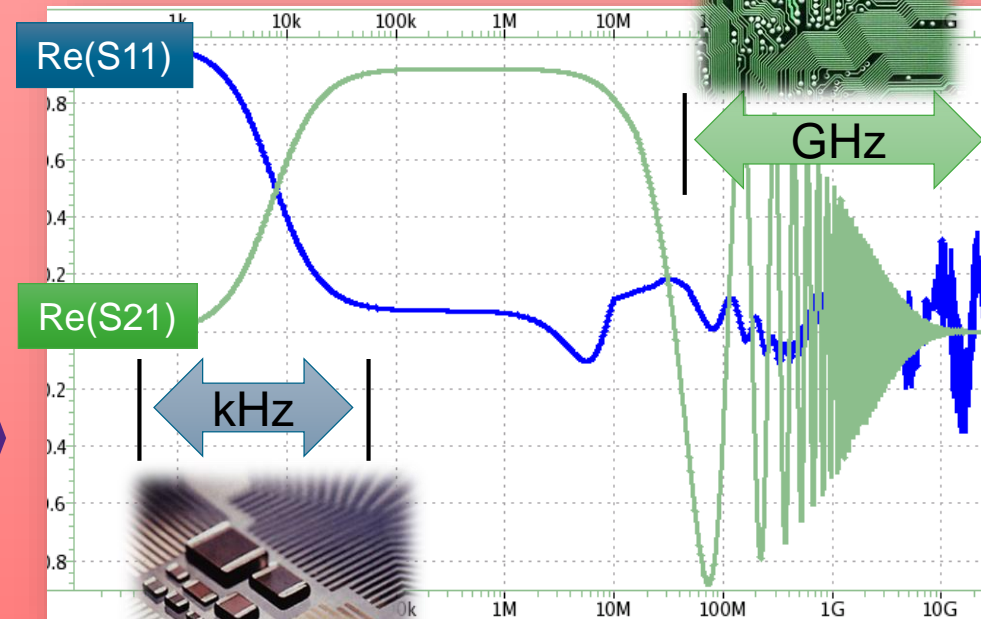


deCap Creates Ultra-Low Frequency Effect

- **Decoupling Capacitor** : a **capacitor** used to **decouple** one part of an electrical network (circuit) from another. (Wikipedia)

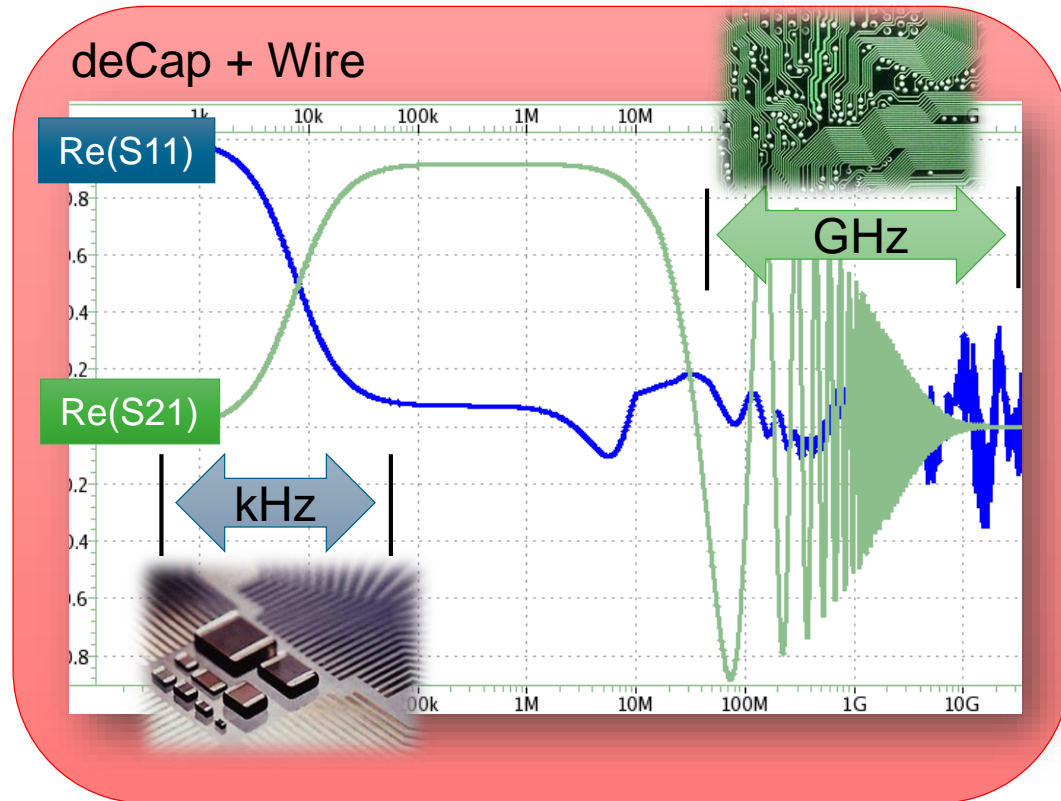


deCap + Wire

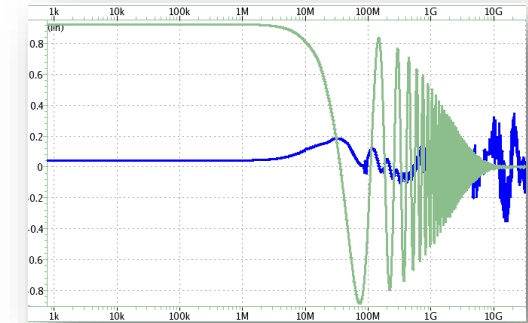


Model separation
→ Accurate sim, convenient for optimization

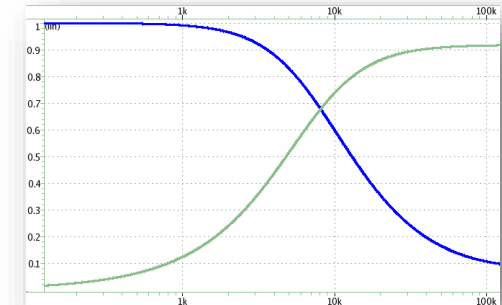
Recommendation: Model Separation



model-1
(wire)



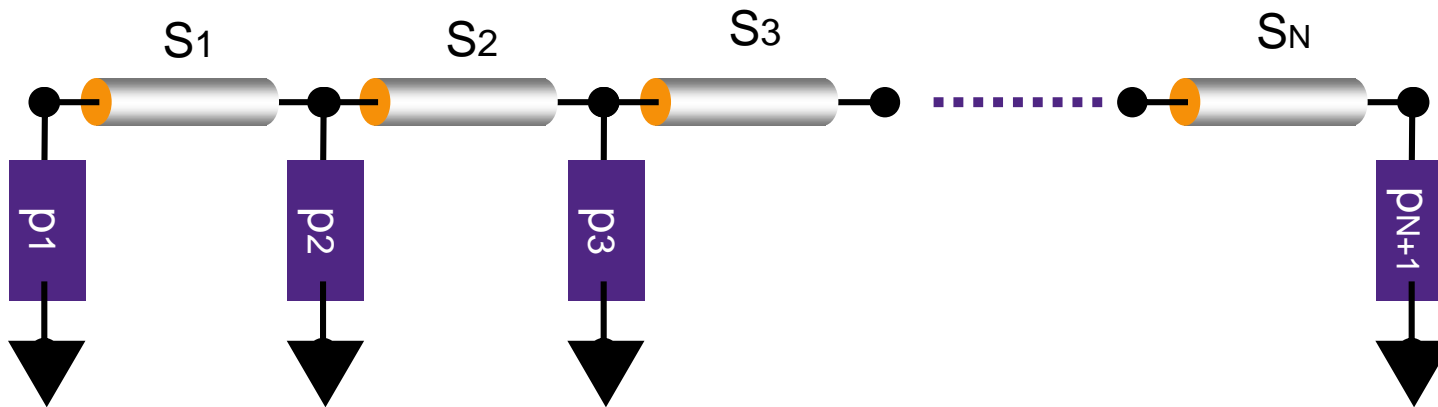
model-2
(deCap)



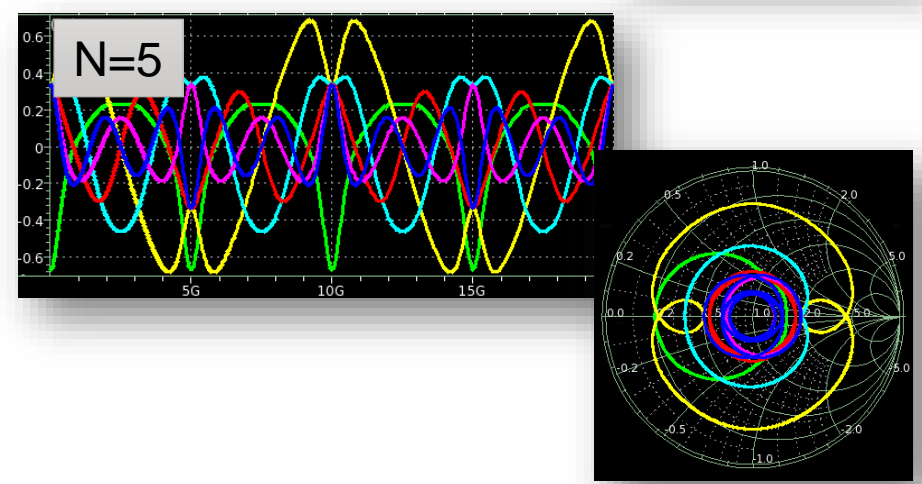
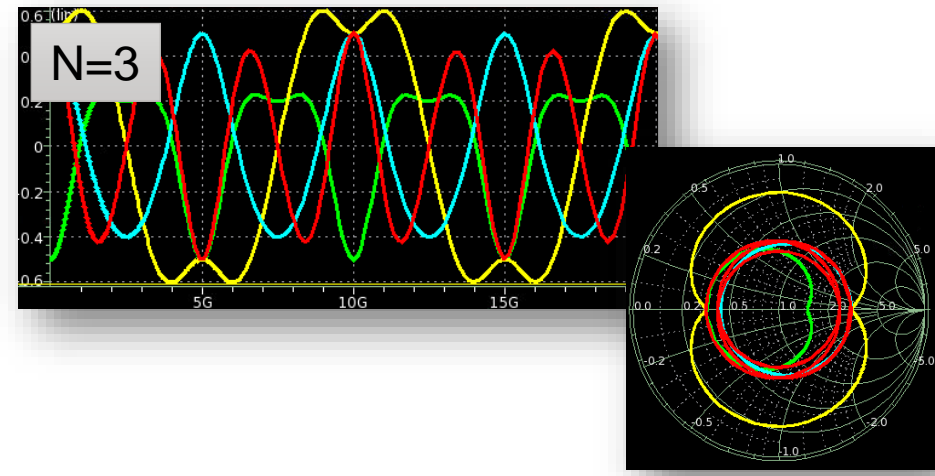
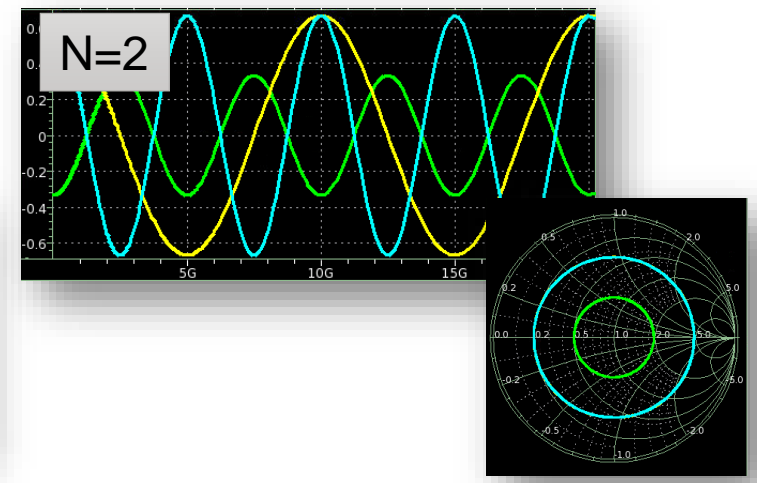
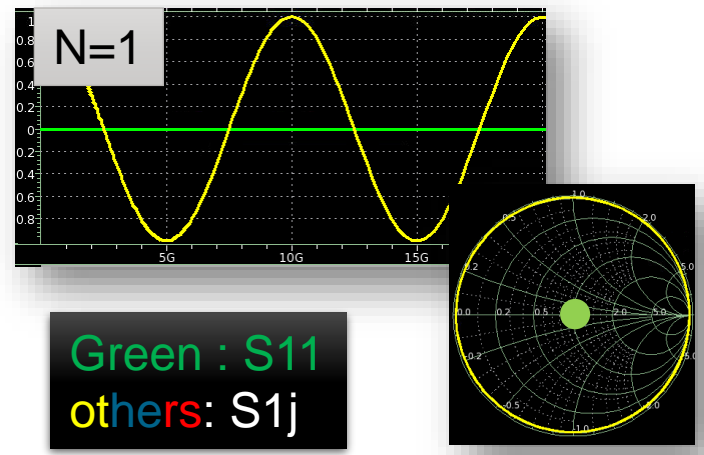
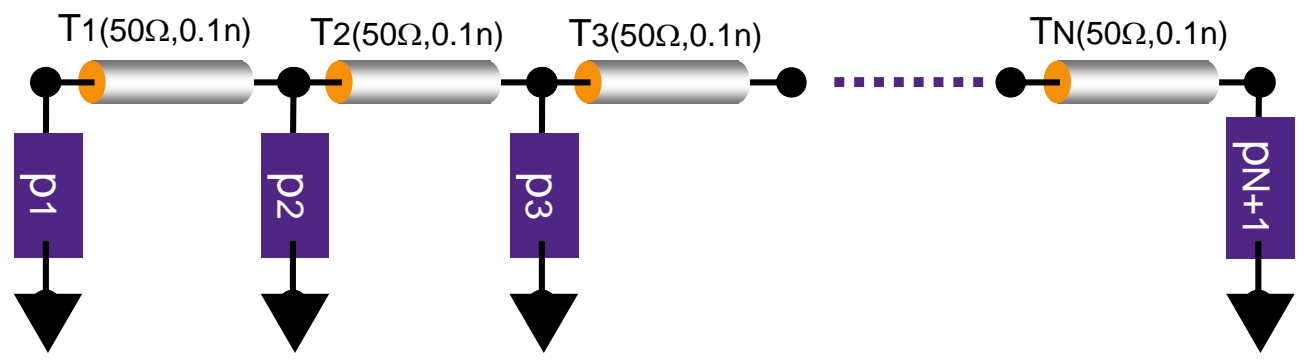
Model separation
→ Fast/Accurate simulation
→ convenient for optimization

Tip 2 : Multi Segment Transmission Lines

Cascading short transmission line segments drastically increase the s-parameter complexity



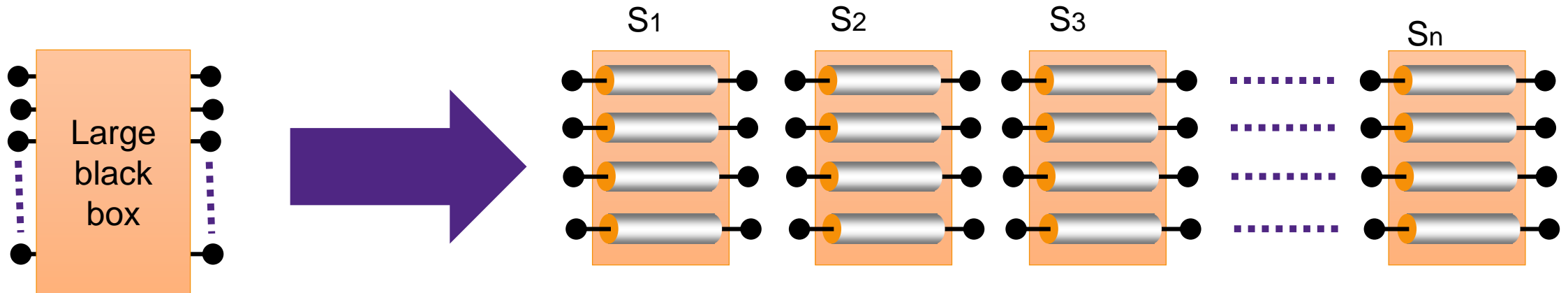
Understanding Multi-Drop S-parameters



# segment	1	2	3	4	20	n
$S(i,i)$	0	-0.33	-0.5	-0.6	-0.91	$-(n-1)/(n+1)$
$S(i,x)$	1	0.66	0.5	0.33	0.095	$2/(n+1)$

Recommendation: Model Separation

When possible, separate s-parameter for each bus segment is recommended

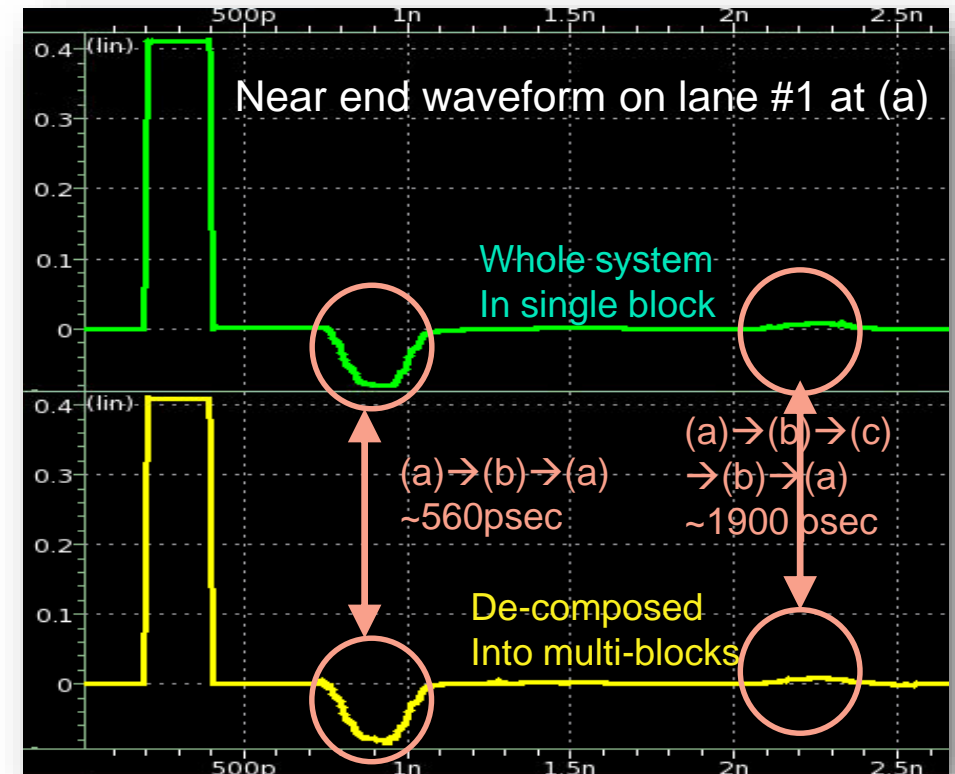
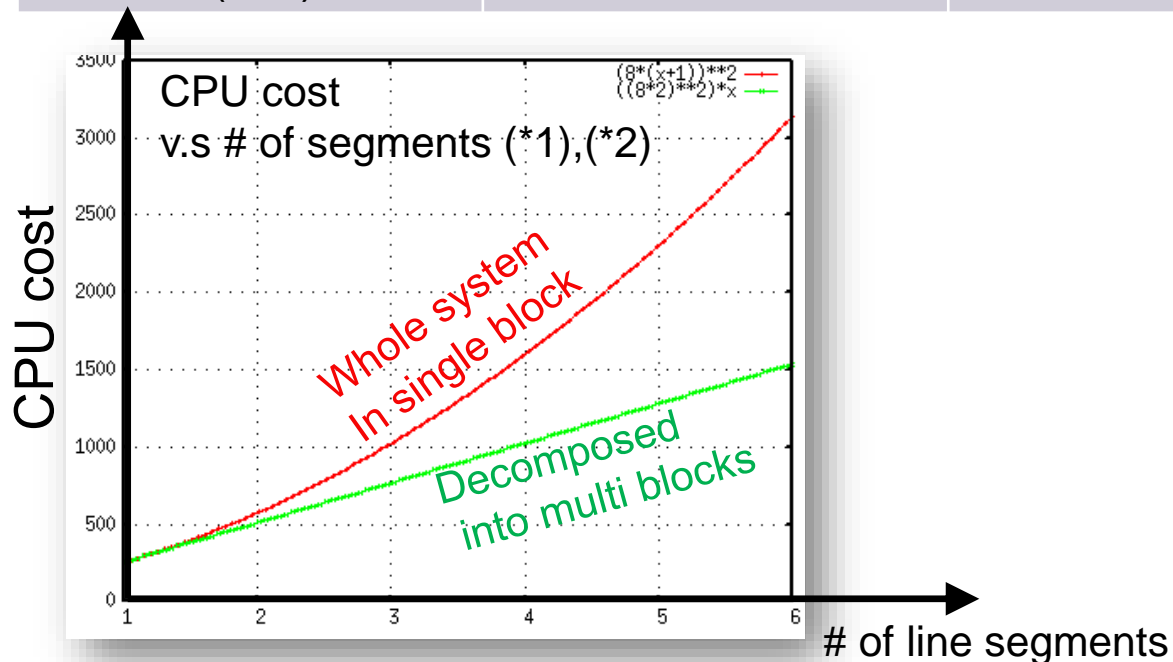


Simulation Performance with Model Separation

Performance and Accuracy

- Performance benefit w/ model separation
- Accuracy preserved

	one 12 port s-parameter block	two 8 port s-parameter blocks
1000 bit transient runtime (sec)	69.1	41.51



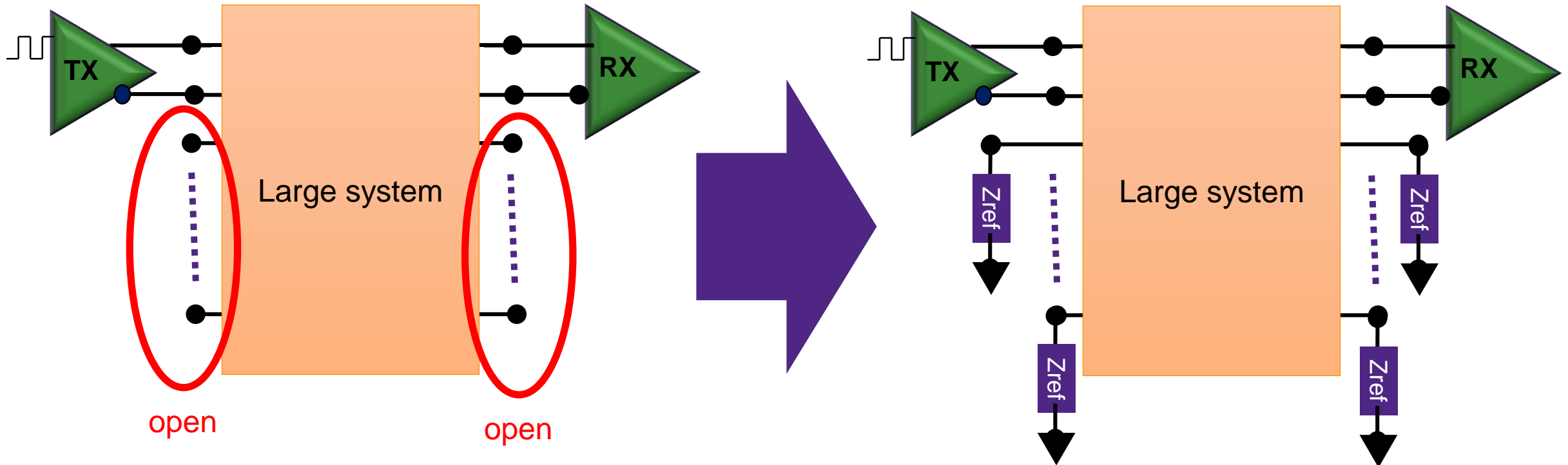
- (*1) These plots assume the same waveform complexity
(*2) Difference may further increase because of high complexity of multi-drop system in single block

Tip 3 : Focusing on Partial Network in Large Systems



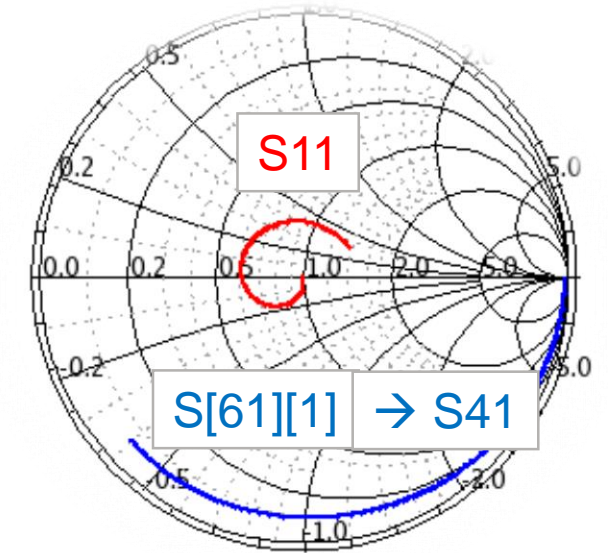
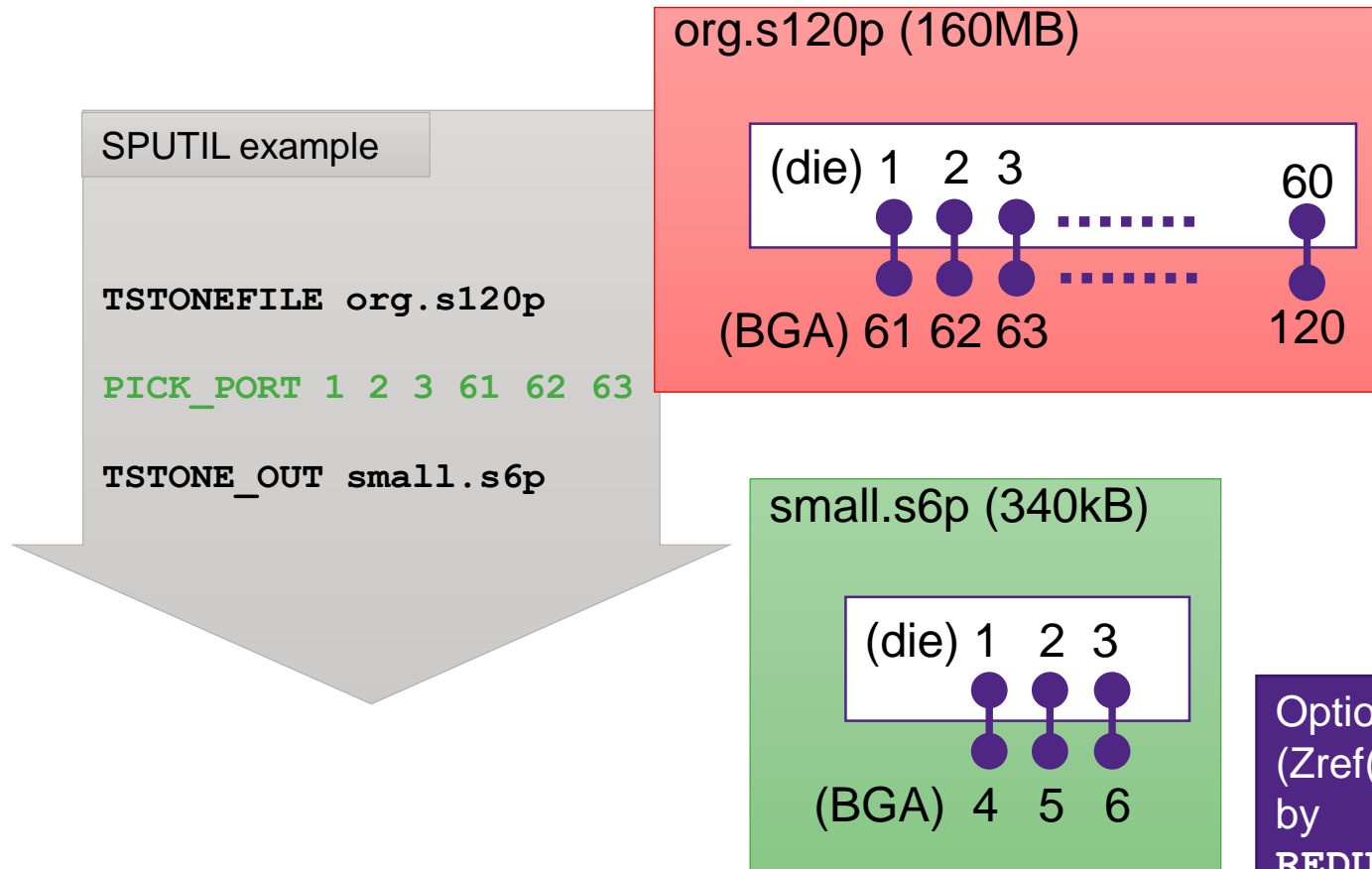
Approach 1: Terminating Unused Ports

- In testing a subset of a big system, many unused s-parameter ports tend to be left open
- Adding proper termination would help simulation stability
 - Add terminations manually
 - Let tools to handle them (*)



Approach 2: Partial Use of Large Systems

- Efficient way for preliminary test
 - Smaller data size, fewer pins → quicker simulation setup & run



Optionally choose termination condition
(Zref(default)/open/short) of port to be removed
by
REDUCE_W_OPEN *indices*
REDUCE_W_SHORT *indices*

Summary

- Introduction
 - Increasing Variation and Complexity in S-parameter modeling
- S-parameter Quality Assessments
 - Passivity, Causality and Reciprocity
- Tips in s-parameter modeling
 - Decoupling Capacitor
 - Multi-segment Transmission Lines
 - Focusing on Partial Network in Large System

Design Success:

- Good Designers
- Good Tools
- Good Understandings

Thank You

